

PN3566

NPN SILICON TRANSISTOR



TO-92 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR PN3566 is a small signal NPN silicon transistor, manufactured by the epitaxial planar process, designed for general purpose amplifier applications where high collector current is required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	600	mA
Power Dissipation	P_D	625	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	Θ_{JA}	200	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=20\text{V}$		50	nA
I_{EBO}	$V_{EB}=5.0\text{V}$		10	μA
BV_{CBO}	$I_C=100\mu\text{A}$	40		V
BV_{CEO}	$I_C=30\text{mA}$	30		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=10\text{mA}$		1.0	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$		0.9	V
h_{FE}	$V_{CE}=10\text{V}, I_C=2.0\text{mA}$	80		
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	150	600	
C_{ob}	$V_{CB}=10\text{V}, I_E=0$		25	pF

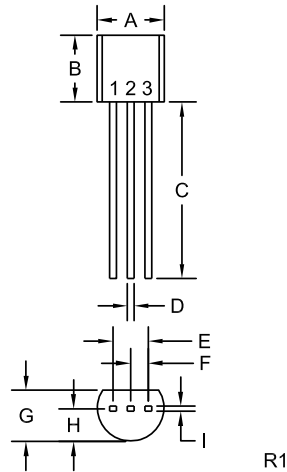
R0 (22-July 2010)

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TO-92 CASE - MECHANICAL OUTLINE



R1

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING:

FULL PART NUMBER

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

R0 (22-July 2010)